07050 TOOLTON (0.505			54	C 074	90	7 0	- 33	
97250 TOSHIBA (DISCF	YTO)	50					- 01	
SILICON NPN EPITAXIAL PLANAR TYPE				29	SC2)1 [.]	17	-
				20			1 /	
					•			
	CATIONS						Unit i	n mr
VHF BAND POWER AMPLIFIER APPL	CATIONS.				Ø 9.39			
FEATURES :					Ø8.5M	AX.		्र
. Output Power : Po=2.8W (Min.)								
(f=175MHz, VCC=13.5V, Pi=0.15W)								1 1
. 100% Tested for Load Mismat				ØQ.4	5		L.BMAX.	74MIN.
Angles with 30:1 VSWR @ Vo	CC=13.5V,	P _o =4W, f=17	5MHz		ΪÅ		1.8	174
					ΨΨ_ 26¥^	x		
				26MAX.				
MAXIMUM RATINGS (Ta=25°C)				[14.3±			
CHARACTERISTIC	SYMBOL	RATING	UNIT	2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2				
Collector-Base Voltage	V _{CBO}	35	v					
Collector-Emitter Voltage	VCEO	17	v					
Emitter-Base Voltage	V _{EBO}	3.5	V Ø508					
Collector Current	IC	0.8	A	1. EMITTER (CASE)				
Collector Power Dissipation (Tc=25°C)	PC	7.5						
Junction Temperature	Тj	175 °C JEDEO EIAJ			, ,,			
Storage Temperature Range	Tstg	-65~175 °C TOSH			IBA 2-9A1B			
		······•		Wei	ght :	3.7g		Ċ
ELECTRICAL CHARACTERISTICS (Ta	a=25 °C)							
CHARACTERISTIC	SYMBOL	TEST CONDITION			MIN.	TYP.	MAX.	נאט
Collector Cut-off Current		$V_{CB}=15V$, $I_E=0$			FILN.	<u> </u>	MAX.	mA
Collector-Base Breakdown Voltage	I _{CBO} V(BR)CBO	$I_{C}=1mA$, $I_{E}=0$			35	-		V
Collector-Emitter Breakdown Voltage	V(BR)CEO	I _C =5mA, I _B =0			17	-	-	v
Emitter-Base Breakdown Voltage	V(BR)EBO	I _E =1mA, I _C =0			3.5	-	-	v
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =0.5A			10	-	-	Γ
Collector Output Capacitance	Cob	$V_{CB}=10V$, $I_{E}=0$, f=1MHz			-	-	15	pF
Output Power	Po	(Fig.)	2.8	3.2	-	W		
Power Gain	Gpe	V _{CC} =13.5V, f=175MHz P ₁ =0.15W			12.7	13.3	-	dB
Collector Efficiency	η _c				60	72	-	2

-421-

|

TOSHIBA {DISCRETE/OPTO}

56C 07491 DT-33-05 9097250 TOSHIBA (DISCRETE/OPTO) 2SC2117

եց

Сз





